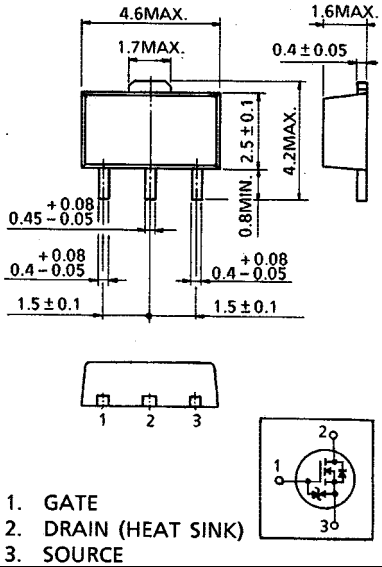
TOSHIBA Field Effect Transistor Silicon N Channel MOS Type (L^2−π−MOSVI)

2SK2964

Chopper Regulator, DC−DC Converter and Motor Drive Applications

- 4 V gate drive
- Low drain−source ON resistance : $R_{DS\ (ON)}$ = 0.13 Ω (typ.)
- High forward transfer admittance : $|Y_{fs}|$ = 2.5 S (typ.)
- Low leakage current : I_{DSS} = 100 μA (max) (V_{DS} = 30 V)
- Enhancement−mode : V_{th} = 0.8~2.0 V (V_{DS} = 10 V, I_D = 1 mA)

Unit: mm



JEDEC	—
JEITA	—
TOSHIBA	2-5K1B

Weight: 0.05 g (typ.)

Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit
Drain−source voltage		V_{DSS}	30	V
Drain−gate voltage (R_{GS} = 20 kΩ)		V_{DGR}	30	V
Gate−source voltage		V_{GSS}	±20	V
Drain current	DC (Note 1)	I_D	2	A
	Pulse (Note 1)	I_{DP}	6	A
Drain power dissipation		P_D	0.5	W
Drain power dissipation (Note 2)		P_D	1.5	W
Single pulse avalanche energy (Note 3)		E_{AS}	56	mJ
Avalanche current		I_{AR}	2	A
Repetitive avalanche energy (Note 4)		E_{AR}	0.05	mJ
Channel temperature		T_{ch}	150	°C
Storage temperature range		T_{stg}	−55~150	°C

Thermal Characteristics

Characteristics	Symbol	Max	Unit
Thermal resistance, channel to ambient	$R_{th\ (ch-a)}$	250	°C / W

Note 1: Please use devices on condition that the channel temperature is below 150°C.

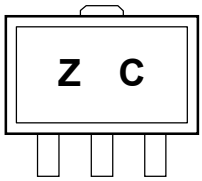
Note 2: Mounted on ceramic substrate (25.4 mm × 25.4 mm × 0.8 mm)

Note 3: V_{DD} = 25 V, T_{ch} = 25°C (initial), L = 10 mH, R_G = 25 Ω, I_{AR} = 2 A

Note 4: Repetitive rating; Pulse width limited by maximum channel temperature.

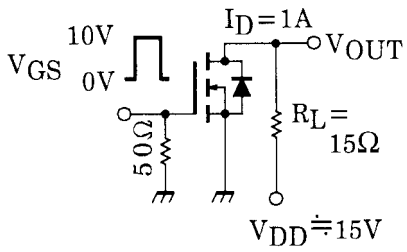
This transistor is an electrostatic sensitive device.
Please handle with caution.

Marking



(The two digits represent the part number.)

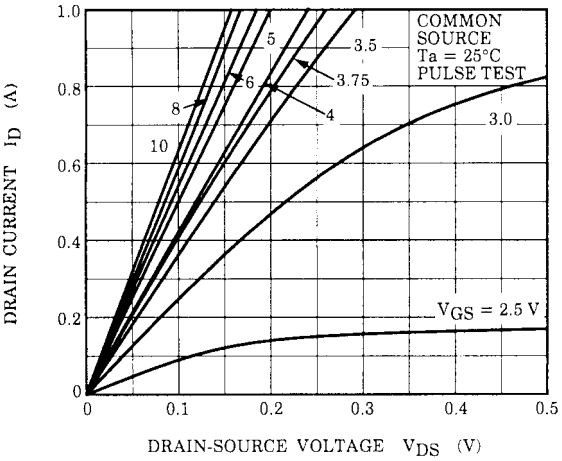
Electrical Characteristics (Ta = 25°C)

Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current		I_{GSS}	V_{GS} = ±16 V, V_{DS} = 0 V	—	—	±10	μA
Drain cut−off current		I_{DSS}	V_{DS} = 30 V, V_{GS} = 0 V	—	—	100	μA
Drain−source breakdown voltage		$V_{(BR)\ DSS}$	I_D = 10 mA, V_{GS} = 0 V	30	—	—	V
Gate threshold voltage		V_{th}	V_{DS} = 10 V, I_D = 1 mA	0.8	—	2.0	V
Drain−source ON resistance		$R_{DS\ (ON)}$	V_{GS} = 4 V, I_D = 1 A	—	0.18	0.25	Ω
			V_{GS} = 10 V, I_D = 1 A	—	0.13	0.18	
Forward transfer admittance		$\|Y_{fs}\|$	V_{DS} = 10 V, I_D = 1 A	1.2	2.5	—	S
Input capacitance		C_{iss}	V_{DS} = 10 V, V_{GS} = 0 V, f = 1 MHz	—	140	—	pF
Reverse transfer capacitance		C_{rss}		—	30	—	
Output capacitance		C_{oss}		—	80	—	
Switching time	Rise time	t_r		—	10	—	ns
	Turn−on time	t_{on}		—	15	—	
	Fall time	t_f		—	85	—	
	Turn−off time	t_{off}		—	195	—	
Total gate charge (gate−source plus gate−drain)		Q_g	V_{DD} ≈ 24 V, V_{GS} = 10 V, I_D = 2 A	—	5.8	—	nC
Gate−source charge		Q_{gs}		—	4.3	—	
Gate−drain (“miller”) Charge		Q_{gd}		—	1.5	—	

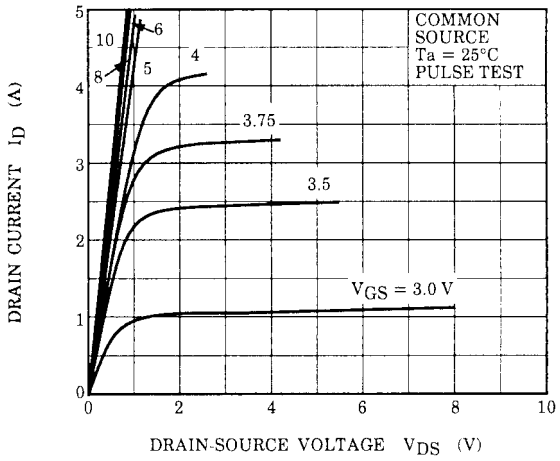
Source−Drain Ratings and Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Continuous drain reverse current (Note 1)	I_{DR}	—	—	—	2	A
Pulse drain reverse current (Note 1)	I_{DRP}	—	—	—	6	A
Forward voltage (diode)	V_{DSF}	I_{DR} = 2 A, V_{GS} = 0 V	—	—	−1.5	V
Reverse recovery time	t_{rr}	I_{DR} = 2 A, V_{GS} = 0 V, dI_{DR} / dt = 50 A / μs	—	50	—	ns
Reverse recovery charge	Q_{rr}		—	20	—	nC

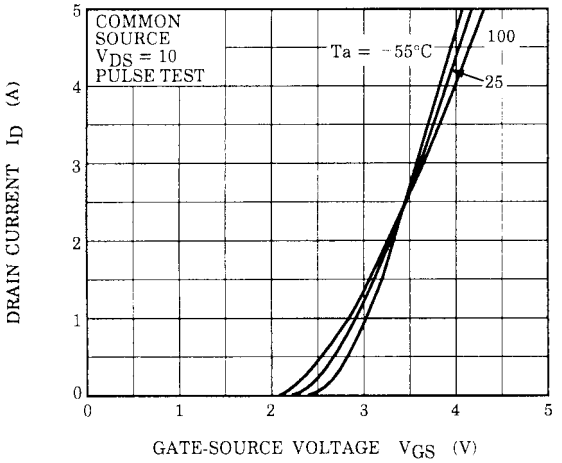
I_D – V_{DS}



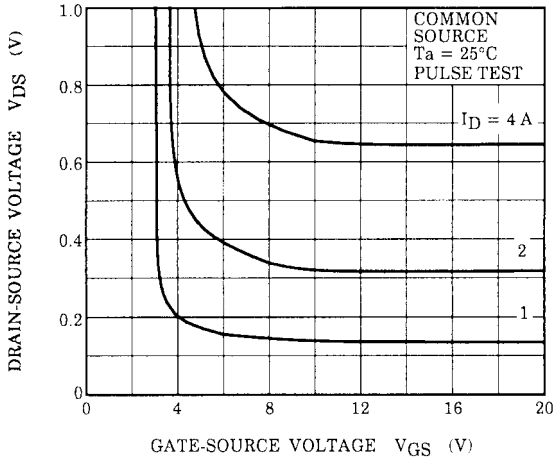
I_D – V_{DS}



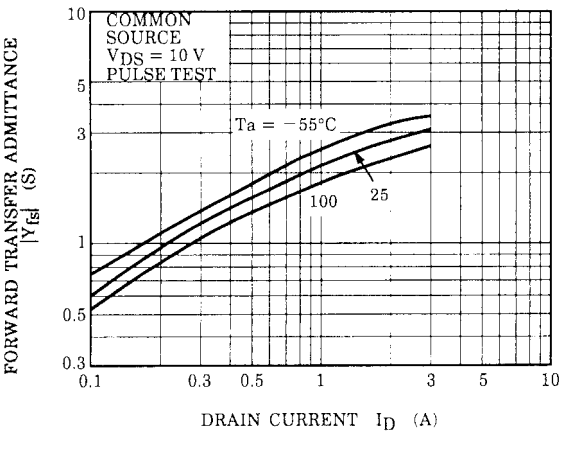
I_D – V_{GS}



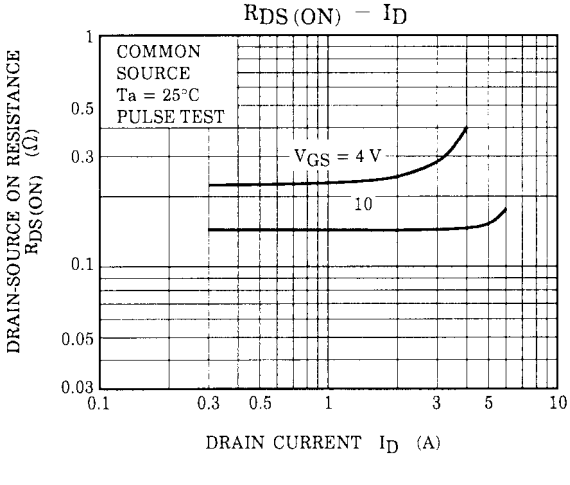
V_{DS} – V_{GS}



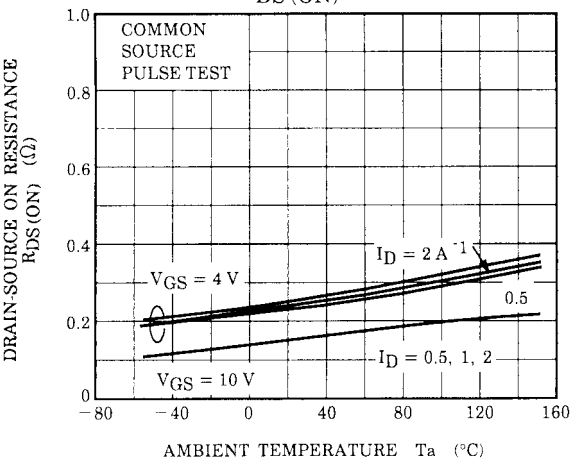
$|Y_{fs}|$ – I_D



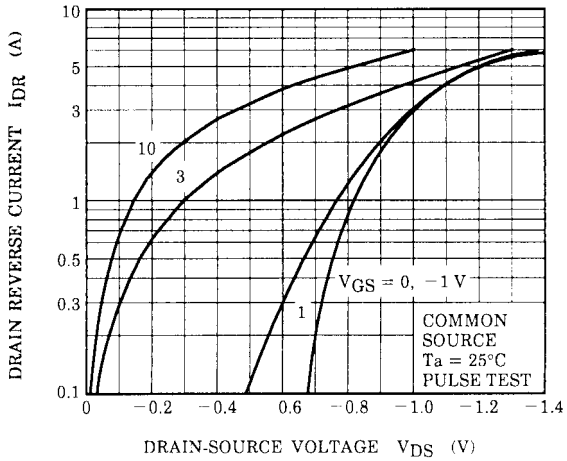
$R_{DS\,(ON)}$ – I_D



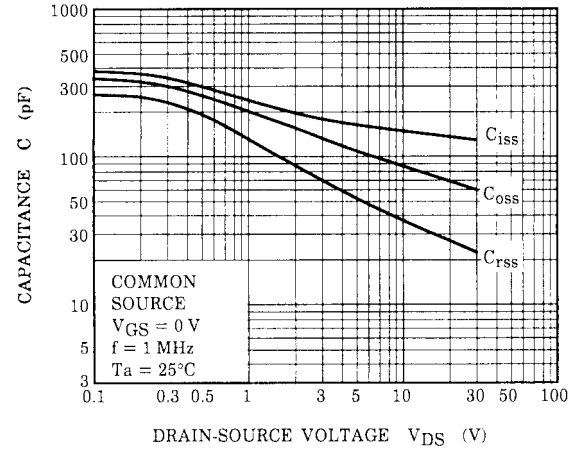
$R_{DS\,(ON)}$ – Ta



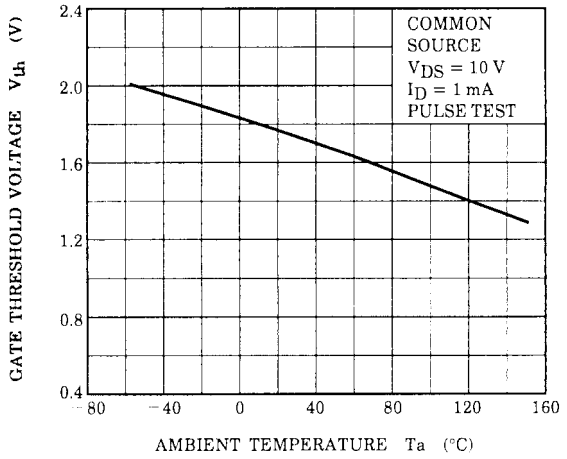
I_{DR} – V_{DS}



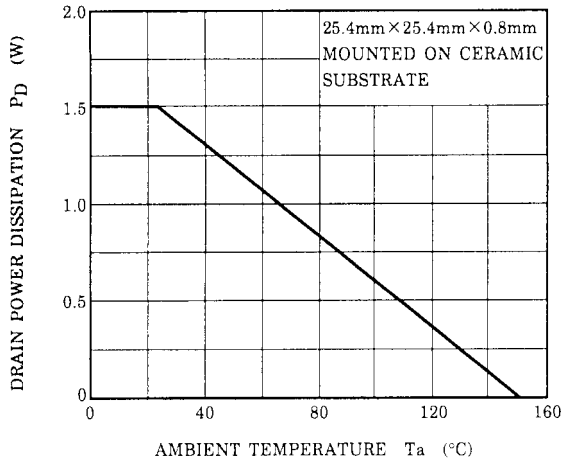
CAPACITANCE – V_{DS}



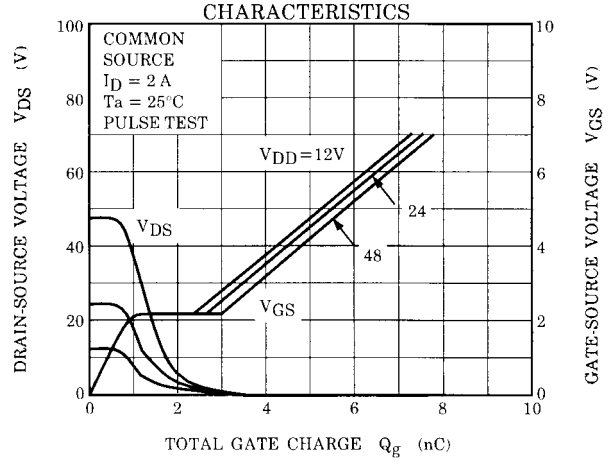
V_{th} – Ta



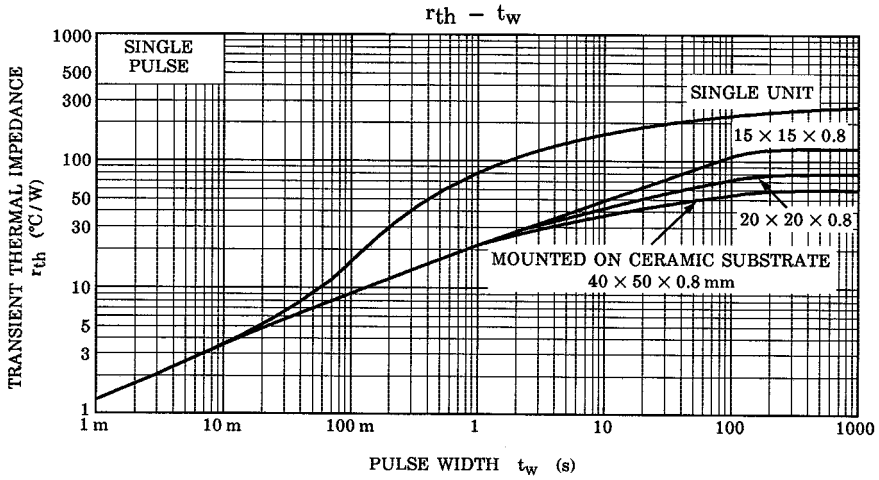
P_D – Ta



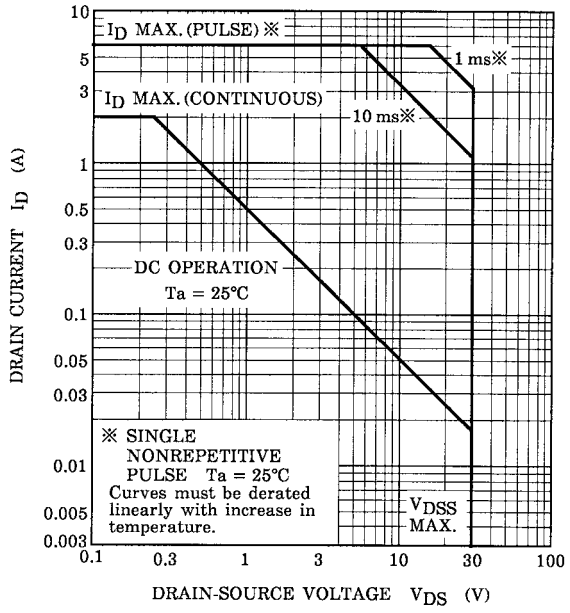
DYNAMIC INPUT / OUTPUT CHARACTERISTICS



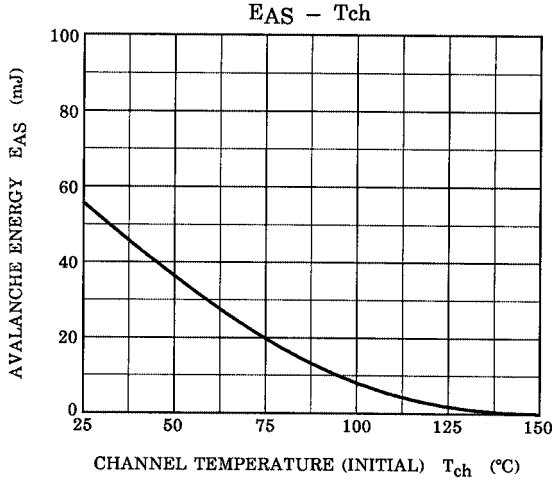
$r_{th} - t_w$

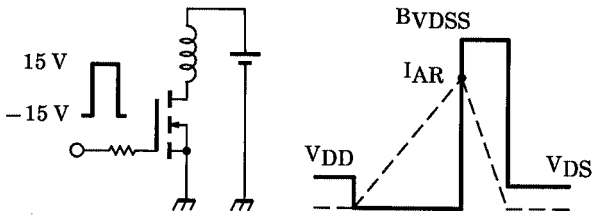


SAFE OPERATING AREA



E_{AS} – Tch





$R_G = 25\ \Omega$
$V_{DD} = 25$ V, L = 10 mH

$$E_{AS} = \frac{1}{2} \cdot L \cdot I^2 \cdot \left(\frac{B_{VDSS}}{B_{VDSS} - V_{DD}} \right)$$

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